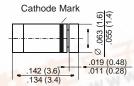
LL41

Schottky Diodes

MiniMELF



Dimensions in inches and (millimeters)

FEATURES

- ♦ For general purpose applications.
- This diode features low turn-on voltage and high breakdown voltage. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- ◆ This diode is also available in the DO-35 case with type designation BAT41.

MECHANICAL DATA

Case: MiniMELF Glass Case (SOD-80)

Weight: approx. 0.05 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

Symbol Valu		Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100 WW.DZ	V
Forward Continuous Current at T _{amb} = 25 °C	I _F	1001)	mA
Repetitive Peak Forward Current at t _p < 1 s, @ < 0.5, T _{amb} = 25 °C	I _{FRM}	350 ¹⁾	mA
Surge Forward Current at t _p = 10 ms, T _{amb} = 25 °C	I _{SFM}	750 ¹⁾	mA
Power Dissipation, T _{amb} = 25 °C	P _{tot}	4001)	mW
Junction Temperature	Tj	125	°C
Ambient Operating Temperature Range	T _{amb}	-65 to +125	°C
Storage Temperature Range	Ts	-65 to +150	°C



LL41

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA / 300 μs Pulses	V _{(BR)R}	100	110	_	V
Forward Voltage Pulse Test $t_p = 300 \ \mu s$ at $I_F = 1 \ mA$ at $I_F = 200 \ mA$	V _F V _F		0.40	0.45 1.0	V
Leakage Current Pulse Test $t_p = 300 \mu s$ at $V_R = 50 V$, at $T_j = 25 ^{\circ}C$ at $V_R = 50 V$, at $T_j = 100 ^{\circ}C$	I _R			100 20	nΑ μΑ
Capacitance at $V_R = 1 V$, $f = 1 MHz$	C _{tot}	-	2	_	pF
Reverse Recovery Time from $I_F = 10$ mA, to $I_R = 10$ mA to $I_R = 1$ mA $R_L = 100$ Ohm	t _{rr}	_	5	_	ns
Thermal Resistance Junction to Ambient Air	R _{thJA}	_	_	3001)	K/W

¹⁾ Valid provided that electrodes are kept at ambient temperature.

